Contents of Applied Physics A 47

This listing presents the papers in alphabetical order of the first author, subdivided according to the groupings "Solids and Materials" and "Surfaces, Interfaces, and Layer Structures". The author index that follows covers Applied Physics A and B, and is presented in tabular form. The names are listed in alphabetical order in the first column. The second column together with the third one contains the bibliographic data necessary to locate the paper. The issue is specified by the number separated from the volume number by a slash. The fourth column states the major PACS number so that the topic of the paper can be inferred by consulting the PACS listing on the left page.

Solids and Materials

Chan Tung N., Caratini Y., D'Anterroches C., Buevoz J.L.:

Characteristics of thin gate dielectric in a rapid thermal processing machine and temperature uniformity studies.

Appl. Phys. A 47/3, 237-247 (1988) PACS: 77.55F 77.50

Danesh P., Kalitzowa M., Pantchev B., Simov S., De Blasi C., Vitali G., Rossi M.:

Dependence of glow discharge Si:H:Cl film morphology on diluent gas and SiCl4 partial pressure.

Appl. Phys. A 47/3, 301-307 (1988) PACS:61.16D 68.55 68.60

Ferreira J.M., Maple M.B., Zhou H., Hake R.R., Lee B.W., Seaman C.L., Kuric M.V., Guertin R.P.:

Magnetic field alignment of high-Tc superconductors RBa2Cu3 07-delta (R=rare earth).

Appl. Phys. A 47/1, 105-110 (1988) PACS: 74.70V 74.30 74.60 Gonczarek R .:

Stoichiometric relations in high-temperature superconducting com-

Appl. Phys. A 47/2, 111-113 (1988) PACS: 74.70 74.30 74.90

Hache F., Ricard D., Flytzanis C., Kreibig U.:

The optical Kerr effect in small metal particles and metal colloids: The case of gold.

Appl. Phys. A 47/4, 347-357 (1988) PACS: 42.65 78.20 82.70 Huber E., Marinero E.E.:

Magneto-optical activity of Ag at the plasma frequency. Appl. Phys. A 47/2, 131-135 (1988) PACS: 78.20L

Landi E., Armigliato A., Solmi S., Kögler R., Wieser E.: Electrical activation of boron-implanted silicon during rapid thermal

Appl. Phys. A 47/4, 359-366 (1988) PACS: 61.70 61.70

Li J.N., Kadowaki K., Menken M.J.V., Huang Y.K., Bakker K., Menovsky A.A., Franse J.J.M.:

Upper critical fields of single-crystalline and polycristalline Ca-Sr-Bi-Cu-O Compounds.

Appl. Phys. A 47/2, 209-211 (1988) PACS: 74.70V 74.60

Litsardakis G., Samaras D., Collomb A., Mignot J.P.:

Manganese location and magnetic structure determination of SrMn2-W hexagonal ferrite by means of neutron diffraction. Appl. Phys. A 47/4, 327-331 (1988) PACS: 75.30

Lu Y.F., Takai M., Nagatomo S., Namba S.:

Wet-chemical etching of Mn-Zn ferrite by focused Ar+-laser irradiation in H3PO4.

Appl. Phys. A 47/4, 319-325 (1988) PACS: 81.40 82.65 Maldonado C.D.:

An analytical technique for the calculation of distributed resistance in a rectangular domain

Appl. Phys. A 47/4, 333-346 (1988) PACS: 85.40 41.00

Mück M., Rogalla H., Heiden C.:

A frequency-modulated read-out system for dc SQUIDs. Appl. Phys. A 47/3, 285-289 (1988) PACS: 74.50

Nimtz G., Marquardt P.:

The electron cut-off wavelength transistor.

Appl. Phys. A 47/4, 317-318 (1988) PACS: 72.15R 85.40 85.30 Nowotny J., Rekas M., Weppner W.:

Thermoelectric power of YBa2Cu3Ox in equilibrium with gas phases. Appl. Phys. A 47/2, 205-208 (1988) PACS: 74.70 72.20 61.70

Svob L., Grattepain C., Marfaing Y .:

Diffusion of deuterium in GaAs a molecular gas source. Appl. Phys. A 47/3, 309-311 (1988) PACS: 72.80E 66.30

Trzcinski R., Queisser H.J.:

Charge transport in semiconductor microjunctions.

Appl. Phys. A 47/2, 119-122 (1988) PACS: 73.40L 72.20 72.80

Ullrich B., Schubert E.F., Stark J.B., Cunningham J.E.: Spatial distribution of impurities in delta-doped n-type GaAs. Appl. Phys. A 47/2, 123-129 (1988) PACS: 81.10 73.60 75.30

Ursu I., Alexandrescu R., Draganescu V., Grigoriu C., Mihailescu I.N., Morjan I., Prokhorov A.M., Karlov N.V., Legutchev A.S.:

Laser action on resonant molecular flows through capillaries. Appl. Phys. B 47/1, 61-65 (1988) PACS: 82.651 82.65 Werner I

Schottky barrier and pn-junction I/V-plots - Small signal evaluation. Appl. Phys. A 47/3, 291-300 (1988) PACS: 73.30 73.40

Windscheif J., Wettling W., Jantz W.:

Nondestructive topographic evaluation of ion-implanted layers on GaAs substrates by optical absorption.

Appl. Phys. A 47/2, 115-118 (1988) PACS: 61.70T 61.80 78.65 78.50

Surfaces, Interfaces and Layer Structures

Albano E.V., Mártin H.O.:

Study of recombination reactions of particles absorbed on fractal and multifractal substrata.

Appl. Phys. A 47/4, 399-407 (1988) PACS: 82.65J 66.30

Arita I.H., Hernandez R., Castano V.M.:

Preparation and imaging of macro-bicrystals in thin films. Appl. Phys. A 47/4, 413-417 (1988) PACS: 61.70N

Beier T., Pescia D., Stampanoni M., Vaterlaus A., Meier F.: Ground state magnetic properties of ultrathin fcc Fe and Co films on Cu(001) surfaces.

Appl. Phys. A 47/1, 73-76 (1988) PACS: 73.60 75.70 68.55 Bertel E., Memmel N., Jacob W., Dose V., Netzer F.P., Rosina G., Rangelov G., Astl G., Saalfeld H.:

Alkali metal oxides: Occupied, unoccupied and excited states.

Appl. Phys. A 47/1, 87-89 (1988) PACS: 73.60H 71.70 79.60 78.70 Bertness K.A., Mahowald P.H., McCants C.E., Wahi A.K.,

Kendelewicz T., Lindau I., Spicer W.E.:

Photoenhancement mechanism for oxygen chemisorption on GaAs (110) using visible light.

Appl. Phys. A 47/3, 219-228 (1988) PACS: 73.50G 68.45 82.50

Dorbath K., Häfele H.-G., Tacke M., Lambrecht A.:

Nonlinear optical studies of relaxation times of carriers in MBE layers of PbSe and PbEuSe

Appl. Phys. A 47/4, 387-391 (1988) PACS: 72.80J 42.65

Eiswirth M., Ertl G.:

Dynamic order in a surface process.

Appl. Phys. A 47/1, 91-94 (1988) PACS: 82.65J 82.20 68.35

Förster A., Lavet J.M., Lüth H.:

The effect of inhomogeneous dopant profiles on the electron energy loss spectra on Si(100).

Appl. Phys. A 47/1, 95-97 (1988) PACS: 72.90 73.90 71.45

Foulon F., Slaoui A., Fogarassy E., Fuchs C., Siffert P.:

Analysis of UV-laser induced oxidation of implanted silicon by optical reflectivity measurements.

Appl. Phys. A 47/3, 255-258 (1988) PACS: 81.60 61.80 78.70

Freund H.-J., Neumann M.:

Photoemission of molecular adsorbates.

Appl. Phys. A 47/1, 3-23 (1988) PACS: 73.20 79.60 82.65 Frev H .:

High rate primary ion beam deposition of a-Si:H films.

Appl. Phys. A 47/2, 193-197 (1988) PACS: 68.55 72.40 81.15

Germann R., Forchel A., Weimann G.

Bevel fabrication for depth resolved studies of multiple quantum well structures.

Appl. Phys. A 47/4, 373-376 (1988) PACS: 78.55D 71.35 81.60

Germar R., Dürr W., Krewer J.W., Pescia D., Gudat W.:

Layer-by-layer growth of metal overlayers.

Appl. Phys. A 47/4, 393-398 (1988) PACS: 68.55

Haag C., Suhr H.:

Improved adhesion of Cu on pre-etched polytetrafluoroethylene by PECYD deposited thin metallic layers.

Appl. Phys. A 47/2, 199-203 (1988) PACS: 81.15G 52.90 68.55

Harris I

On the adsorption and desorption of H2 at metal surfaces. Appl. Phys. A 47/1, 63-71 (1988) PACS: 82.65M 68.35 82.20 Inushima T., Hirose N., Urata K., Ito K., Yamazaki S.:

Film growth mechanism of photo-chemical vapor deposition. Appl. Phys. A 47/3, 229-236 (1988) PACS: 81.15G 82.30 82.60

Kempf J., Nonnenmacher M., Wagner H.H.: Thin film characterization by laser interferometry combined with SIMS

Appl. Phys. A 47/2, 137-145 (1988) PACS: 07.75 78.65

Kissel J., Zscheeg H., Rüdenauer F.G.:

Pulsed operation of a liquid metal ion source. Appl. Phys. A 47/2, 167-169 (1988) PACS: 79.40

Konstantinov L., Nowak R., Hess P.:

Film growth and mechanism of LICVD of chromium films from Cr(CO)6 at 248 nm.

Appl. Phys. A 47/2, 171-181 (1988) PACS: 81.15 82.40 82.65 Kullmer R., Bauerle D.:

Excimer-laser-induced ablation of the high-Tc superconductor Bi-Ca-Sr-Cu-O.

Appl. Phys. A 47/1, 103-104 (1988) PACS: 74.70 42.60 82.65

Kullmer R., Bäuerle D.: Laser-induced chemical etching of silicon in chlorine atmosphere III. Combined CW and pulsed irradiation.

Appl. Phys. A 47/4, 377-386 (1988) PACS: 81.60 82.65 42.60

Marx A., Krüger J.K., Unruh H.-G.:

Brillouin spectroscopy on monodomains of thin polycrystalline layers of molecular crystals.

Appl. Phys. A 47/4, 367-371 (1988) PACS: 78.35 62.20

Mavroyannis C.:

Optical excitation spectra of rare-gas atoms physisorbed on metal surfaces. Numerical results.

Appl. Phys. A 47/2, 157-165 (1988) PACS: 68.35 73.20 78.65 Micheli F., Boyd I.W .:

In-situ monitoring of laser-induced silicon oxidation.

Appl. Phys. A 47/3, 249-253 (1988) PACS: 07.60H 81.60 Rendulic K.D.:

The influence of surface defects on adsorption and desorption. Appl. Phys. A 47/1, 55-62 (1988) PACS: 68.10J 68.45 82.65

Sankur H., Cheung J.T.:

Formation of dielectric and semiconductor thin films by laser-assisted

Appl. Phys. A 47/3, 271-284 (1988) PACS: 68.55 81.15

Snowdon K.J., O'Connor D.J., MacDonald R.J.: Observation of transient absorption or skipping motion in small angle

ion-surface scattering. Appl. Phys. A 47/1, 83-85 (1988) PACS: 79.20R 34.50 34.70 79.80 So S.K., Ho W.:

Photon-induced reactions of NO adsorbed on GaAs(110). Appl. Phys. A 47/3, 213-217 (1988) PACS: 79.20D 73.25 78.65

Umbach E.:

Electronic structure and interactions in well-defined coadsorbate layers. Appl. Phys. A 47/1, 25-36 (1988) PACS: 82.65 68.35 79.60 82.80 Veen G.N.A. van, Baller T.S., Dieleman J.:

A time-of-flight study on the nanosecond laser induced etching of Cu with Cl2 at 308 nm.

Appl. Phys. A 47/2, 183-192 (1988) PACS: 66.00 79.20

Wautelet M., Laude L.D., Hanus F., Heinig K.-H.: Negative thermal feedback in laser-assisted oxidation in thin Zn films.

Appl. Phys. A 47/3, 313-316 (1988) PACS 81.60 82.65 42.60 Wintterlin J., Brune H., Höfer H., Behm R.J.: Atomic scale characterization of oxygen adsorbates on Al(111) by

scanning tunneling microscopy. Appl. Phys. A 47/1, 99-102 (1988) PACS: 61.16D 82.65 73.20

Wurm S., Alpern P., Savignac D., Kakoschke R.:

Modulated optical reflectance measurements on amorphous silicon layers and detection of residual defects.

Appl. Phys. A 47/2, 147-155 (1988) PACS: 78.50G 78.65 68.55 Young E.M.:

Electron-active silicon oxidation.

Appl. Phys. A 47/3, 259-269 (1988) PACS: 68.55b 79.60 34.80 Zacharias H.:

Laser spectroscopy of desorbing molecules Appl. Phys. A 47/1, 37-54 (1988) PACS: 33.20 82.65

Zafar N., Chevallier J., Jacobsen F.M., Charlton M., Laricchia G.: Experimentation with thin single crystal W foils as slow positron transmission mode moderators.

Appl. Phys. A 47/4, 409-412 (1988) PACS: 78.70 81.40 07.77

Zimny R., Hagedorn H., Winter H., Kirschner J.:

Capture of polarized electrons from FE(110) into excited terms of fast atoms scattered at grazing incidence.

Appl. Phys. A 47/1, 77-81 (1988) PACS: 79.20N 75.50 34.50

